

HIGH-SPEED 3.3V 64/32K x 9 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

IDT70V9189/79L

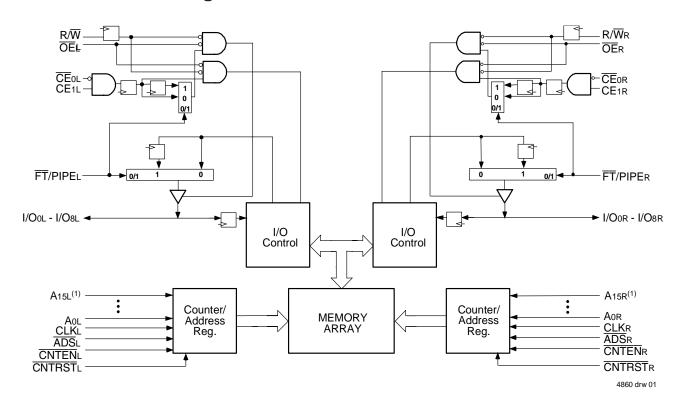
Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 6.5/7.5/9/12ns (max.)
 - Industrial: 9ns (max.)
- Low-power operation
 - IDT70V9189/79L Active: 500mW (typ.) Standby: 1.5mW (typ.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without

additional logic

- Full synchronous operation on both ports
 - 4ns setup to clock and 0ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 6.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 10ns cycle time, 100MHz operation in Pipelined output mode
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP)

Functional Block Diagram



NOTE:

1. A₁₅x is a NC for IDT70V9179.

FEBRUARY 2004

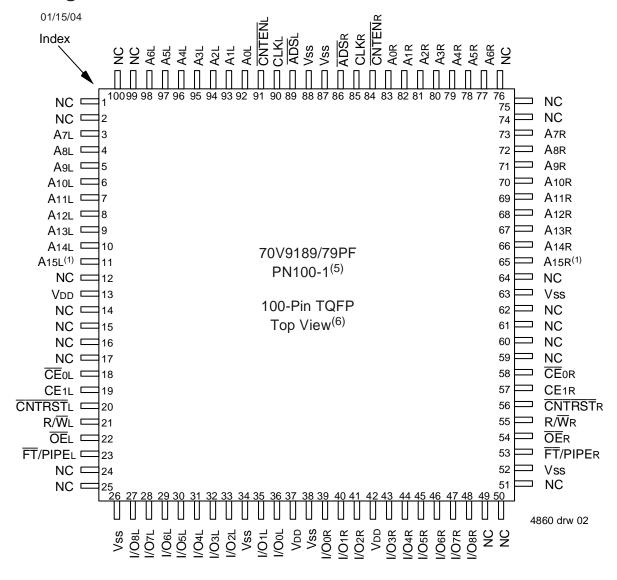
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Description:

The IDT70V9189/79 is a high-speed $64/32K \times 9$ bit synchronous Dual Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9189/79 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}_0$ and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 500mW of power.

Pin Configuration^(2,3,4)



- 1. A_{15x} is a NC for IDT70V9179.
- 2. All Vcc pins must be connected to power supply.
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names				
CE0L, CE1L	CEOR, CE1R	Chip Enables				
R/WL	R/WR	Read/Write Enable				
ŌĒL	OE R	Output Enable				
A0L - A15L ⁽¹⁾	A0R - A15R ⁽¹⁾	Address				
I/O0L - I/O8L	I/O0R - I/O8R	Data Input/Output				
CLKL	CLKR	Clock				
ADSL	ĀDSR	Address Strobe Enable				
CNTENL	CNTENR	Counter Enable				
CNTRSTL	<u>CNTRST</u> R	Counter Reset				
FT/PIPEL	FT/PIPER	Flow-Through / Pipeline				
V	DD	Power (3.3V)				
V	SS	Ground (0V)				

NOTE:

- 1. Address A₁₅x is NC for IDT70V9179.
- 2. $\overline{\text{LB}}$ and $\overline{\text{UB}}$ are single buffered regardless of state of $\overline{\text{FT}}/\text{PIPE}$.
- CEo and CE1 are single buffered when FT/PIPE = VIL,
 CEo and CE1 are double buffered when FT/PIPE = VIH,
 i.e. the signals take two cycles to deselect.

4860 tbl 01

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	Œ	CE ₁	R/W	I/O ₀₋₈	MODE			
Х	↑	Н	Х	Χ	High-Z	Deselected-Power Down			
Х	↑	Χ	L	Χ	High-Z	High-Z Deselected-Power Down			
Х	↑	L	Н	L	DATAIN	Write			
L	↑	L	Н	Н	DATAout	Read			
Н	Χ	L	Н	Χ	High-Z	Outputs Disabled			

NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. ADS, CNTEN, CNTRST = X.
- 3. $\overline{\text{OE}}$ is an asynchronous input signal.

Truth Table II—Address Counter Control^(1,2,3)

External Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE		
An	Х	An	↑	L ⁽⁴⁾	Х	Н	Di/o (n)	External Address Used		
Х	An	An + 1	↑	Н	L ⁽⁵⁾	Н	Dvo(n+1)	Counter Enabled—Internal Address generation		
Х	An + 1	An + 1	↑	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)		
Х	Х	A0	↑	Х	Х	L ⁽⁴⁾	DI/O(0)	Counter Reset to Address 0		

NOTES:

4860 tbl 03

4860 tbl 02

- 1. "H" = V_{IH} , "L" = V_{IL} , "X" = Don't Care.
- 2. $\overline{\text{CE}}_0$ and $\overline{\text{OE}}$ = V_{IL}; CE₁ and R/ $\overline{\text{W}}$ = V_{IH}.
- 3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. ADS and CNTRST are independent of all other signals including CEo and CE1.
- 5. The address counter advances if $\overline{\text{CNTEN}}$ = V_{IL} on the rising edge of CLK, regardless of all other signals including $\overline{\text{CE}}_0$ and CE1.

Recommended Operating Temperature and Supply Voltage

Grade	Ambient Temperature ⁽²⁾	GND	V DD
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

NOTES

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
VIH	Input High Voltage	2.0V	_	Vcc+0.3V ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	٧

4860 tbl 05

NOTES

4860 tbl 04

- 1. $V_{IL} \ge -1.5V$ for pulse width less than 10 ns.
- 2. VTERM must not exceed VDD +0.3V.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	٧
TBIAS	Temperature Under Bias	-55 to +125	°C
Тѕтс	Storage Temperature	-65 to +150	°C
TJN	Junction Temperature	+150	°C
Іоит	DC Output Current	50	mA

4860 tbl 06

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed VDD +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to < 20mA for the period of VTERM > VDD + 0.3V.
- 3. Ambient Temperature Under DC Bias. NO AC Conditions. Chip Deselected.

Capacitance⁽¹⁾ (TA = +25°C, f = 1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

NOTES:

- These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 0.3V)

			70V9189/79L		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	$V_{DD} = 3.6V$, $V_{IN} = 0V$ to V_{DD}	_	5	μΑ
llo	Output Leakage Current	$\overline{\text{CE}}$ = ViH or CE1 = ViL, VouT = 0V to VDD	_	5	μΑ
Vol	Output Low Voltage	IoL = +4mA	_	0.4	٧
Vон	Output High Voltage	IOH = -4mA	2.4	_	V

NOTE

1. At VDD ≤ 2.0V input leakages are undefined.

4860 tbl 08

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range(3) (VDD = 3.3V ± 0.3V)

						89/79L6 I Only		89/79L7 I Only		39/79L9 & Ind		9/79L12 Only	
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
Icc	Dynamic Operating	CEL and CER= VIL,	COM'L	L	220	350	200	310	180	260	150	230	mA
	Current (Both Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	L	_	_	_	_	180	280	_	_	
ISB1	Standby Current	CEL = CER = VIH	COM'L	L	70	130	65	130	50	100	40	80	mA
	(Both Ports - TTL Level Inputs)	f = fmax ⁽¹⁾	IND	L	_	_	_	_	50	120	_	_	
ISB2	Standby Current (One	$\overline{\underline{CE}}$ "A" = VIL and $\overline{\overline{CE}}$ "B" = VIH ⁽⁵⁾	COM'L	L	150	250	140	245	110	190	100	175	mA
	Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L			_		110	205			
ISB3	Full Standby Current (Both	Both Ports CEL and CER > VDD - 0.2V,	COM'L	L	0.4	3	0.4	3	0.4	3	0.4	3	mA
	Ports - CMOS Level Inputs)	$VIN \ge VDD - 0.2V \text{ or } VIN \le 0.2V, f = 0^{(2)}$	IND	L			_		0.4	6			
ISB4	Full Standby $\overline{\mathbb{CE}}^*A^* \leq 0.2V$ and $\overline{\mathbb{CE}}^*B^* \geq VDD - 0.2V^{(!)}$		COM'L	L	140	240	130	235	100	180	90	165	mA
	Port - CMOS Level Inputs)	$\begin{array}{l} \text{VIN} \geq \text{VDD} - 0.2 \text{V or} \\ \text{VIN} \leq 0.2 \text{V, Active Port,} \\ \text{Outputs Disabled, f = fMAX}^{(1)} \end{array}$	IND	L	_	_	_	_	100	195	_	_	

4860 tbl 09 NOTES:

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. Icc Dc(f=0) = 90mA (Typ).
- 5. $\overline{CE}x = V_{IL}$ means $\overline{CE}_{0x} = V_{IL}$ and $CE_{1x} = V_{IH}$ $\overline{CE}x = V_{IH}$ means $\overline{CE}_{0x} = V_{IH}$ or $CE_{1x} = V_{IL}$

 - $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{Vcc}$ 0.2 V
 - $\overline{\text{CE}}$ x \geq VDD 0.2V means $\overline{\text{CE}}$ 0x \geq VDD 0.2V or CE1x \leq 0.2V
 - "X" represents "L" for left port or "R" for right port.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

4860 tbl 10

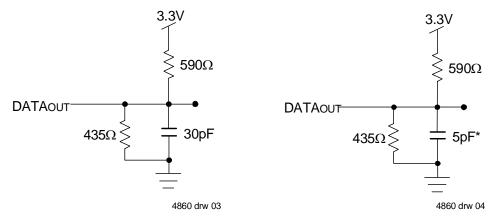


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz).
*Including scope and jig.

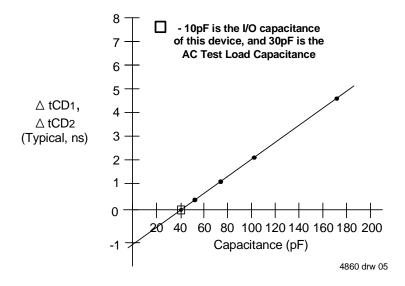


Figure 3. Typical Output Derating (Lumped Capacitive Load).

4860 tbl 11

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3)}$ (VDD = 3.3V ± 0.3V, TA = 0°C to +70°C)

•		70V91	89/79L6 I Only	70V9189/79L7 Com'l Only		70V9189/79L9 Com'l & Ind		70V9189/79L12 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19	_	22	_	25	_	30	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	10	_	12	_	15	_	20	_	ns
tcH1	Clock High Time (Flow-Through) ⁽²⁾	6.5	_	7.5	_	12	_	12	_	ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	6.5	_	7.5	_	12	_	12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4	_	5	_	6	_	8	_	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	4		5	_	6	_	8		ns
tr	Clock Rise Time	_	3	_	3	_	3	_	3	ns
tF	Clock Fall Time	_	3		3		3		3	ns
tsa	Address Setup Time	3.5	_	4	_	4	_	4		ns
tha	Address Hold Time	0	_	0	_	1	_	1	_	ns
tsc	Chip Enable Setup Time	3.5	_	4	_	4	_	4	_	ns
thc	Chip Enable Hold Time	0	_	0	_	1	_	1	_	ns
tsw	R/W Setup Time	3.5	_	4	_	4	_	4		ns
thw	R/W Hold Time	0	_	0	_	1	_	1	_	ns
tsp	Input Data Setup Time	3.5	_	4	_	4	_	4	_	ns
tho	Input Data Hold Time	0	_	0	_	1	_	1	_	ns
tsad	ADS Setup Time	3.5	_	4	_	4	_	4	_	ns
thad	ADS Hold Time	0	_	0	_	1	_	1	_	ns
tscn	CNTEN Setup Time	3.5	_	4	_	4	_	4	_	ns
thcn	CNTEN Hold Time	0	_	0	_	1	_	1	_	ns
tsrst	CNTRST Setup Time	3.5	_	4	_	4	_	4	_	ns
thrst	CNTRST Hold Time	0	_	0	_	1	_	1	_	ns
toe	Output Enable to Data Valid		6.5		9	_	12	_	12	ns
toLZ	Output Enable to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	2		ns
tonz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾	_	15		18		20	_	25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾	_	6.5		7.5		9		12	ns
toc	Data Output Hold After Clock High	2		2	_	2	_	2		ns
tckHz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	2	_	ns
Port-to-Port D	lelay									
tcwdd	Write Port Clock High to Read Data Delay		24		28		35		40	ns
tccs	Clock-to-Clock Setup Time		9		10		15	_	15	ns

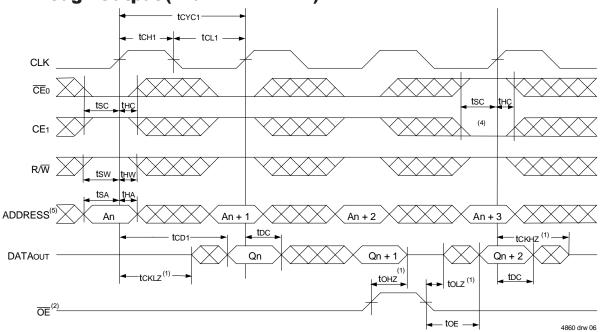
NOTES

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

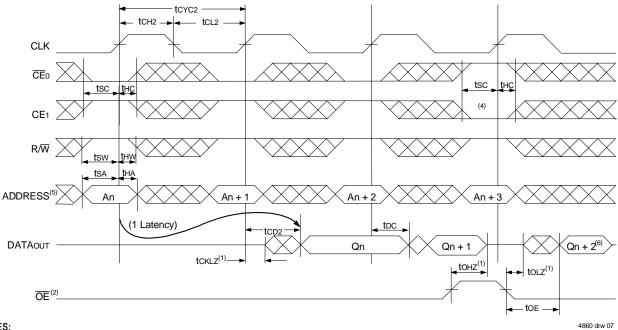
2. The Pipelined output parameters (tcyc2, tcb2) apply to either or both the Left and Right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcb1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER, and FT/PIPEL.

Timing Waveform of Read Cycle for Flow-Through Output (FT/PIPE"x" = VIL)(3,6)

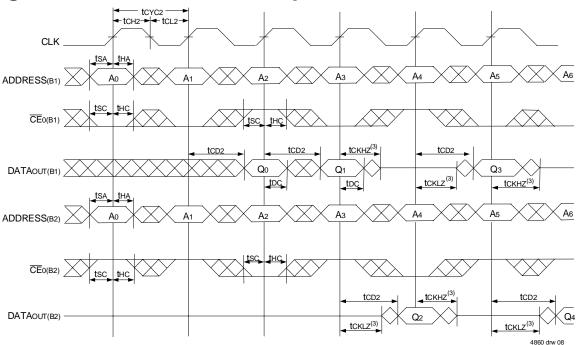


Timing Waveform of Read Cycle for Pipelined Output $(\overline{FT}/PIPE"x" = Vih)^{(3,6)}$

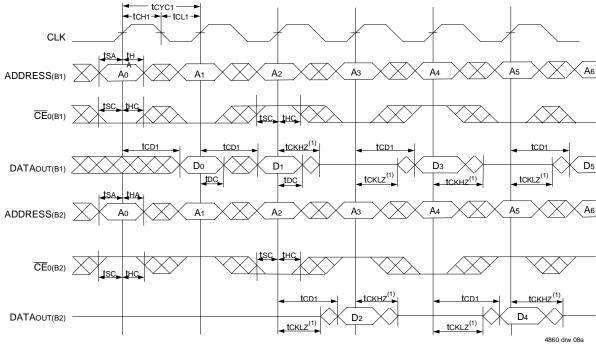


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = V_{IL}$, \overline{CNTEN} and $\overline{CNTRST} = V_{IH}$.
- 4. The output is disabled (High-Impedance state) by \overline{CE}_0 = VIH or CE1 = VIL following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 6. "X' here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



Timing Waveform of a Bank Select Flow-Through Read⁽⁶⁾



- B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9089/79 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{OE}}$ and $\overline{\text{ADS}}$ = VIL; $\overline{\text{CE1(B1)}}$, $\overline{\text{CE1(B2)}}$, $\overline{\text{R/W}}$, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = VIL; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.
- 5. \overline{OE} = V_{IL} for the Right Port, which is being read from. \overline{OE} = V_{IH} for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb.

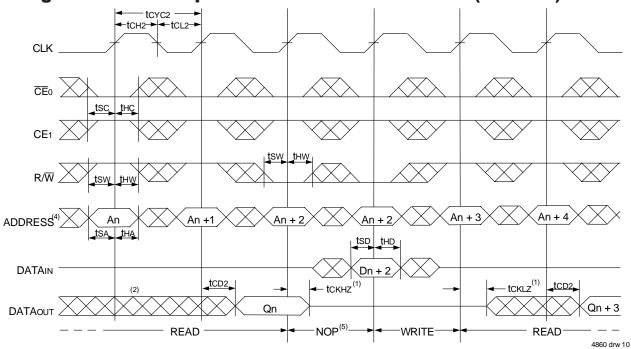
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.

CLK "A" tsw NO MATCH ADDRESS "A" MATCH tsD VALID CLK "B" tCD1 MATCH tcwdd (6). DATAOUT "B" VALID VALID **▼** tDC 4860 drw 09

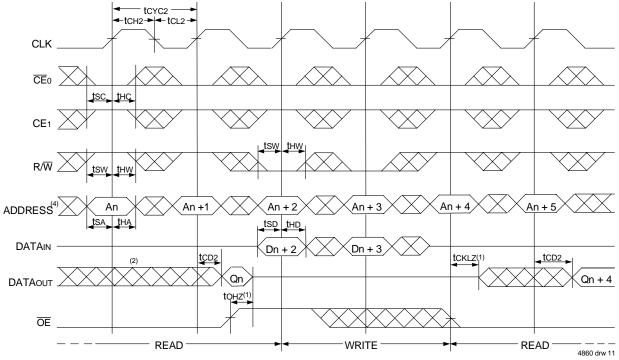
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9189/79 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/ \overline{W} , \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. CEo and ADS = VIL; CE1, CNTEN, and CNTRST = VIH.
- 5. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb.

 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = V_{IL}$)⁽³⁾

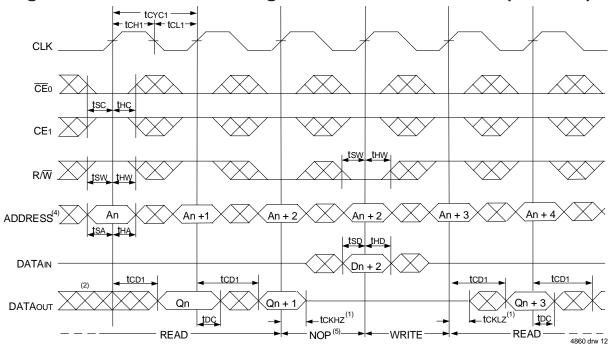


Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

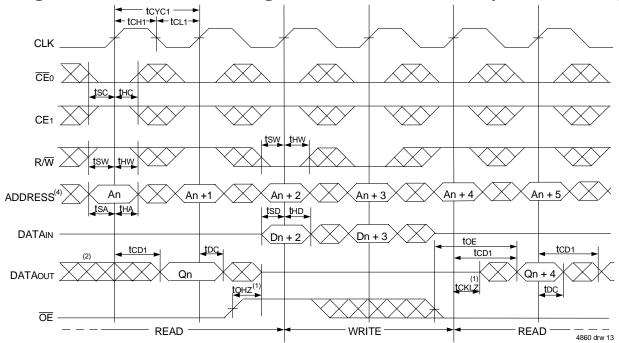


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = V_{IL}; CE₁, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = V_{IH}. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read $(\overline{OE} = V_{IL})^{(3)}$

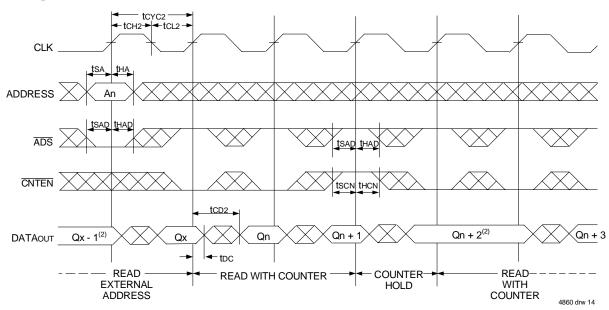


Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{\text{OE}}$ Controlled) $^{(3)}$

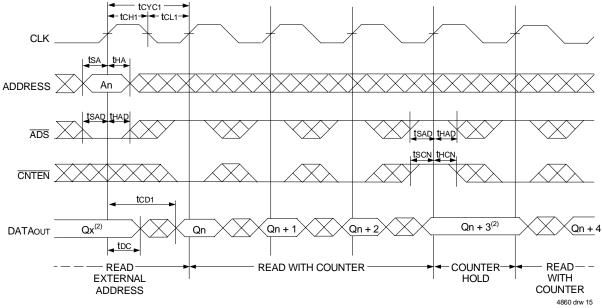


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. CEo and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

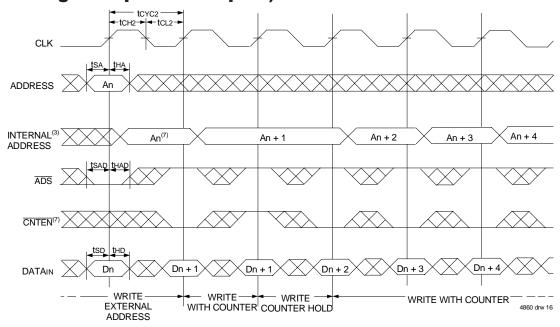


Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾

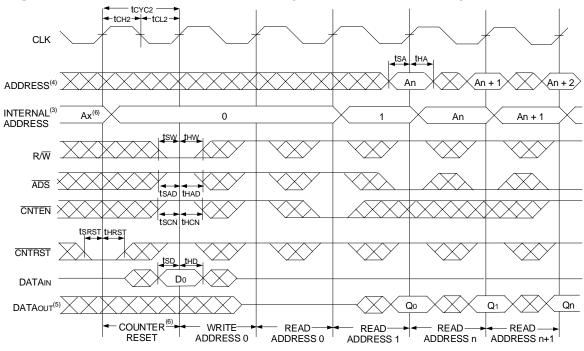


- 1. $\overline{\text{CE}}_0$ and $\overline{\text{OE}}$ = V_{IL}; CE₁, R/ $\overline{\text{W}}$, and $\overline{\text{CNTRST}}$ = V_{IH}.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- 1. $\overline{CE_0}$ and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.
- 2. \overline{CE}_0 = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = V_{IL} constantly loads the address on the rising edge of the CLK, numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = V_{IL} advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance.
 The 'An +1' Address is written to during this cycle.

Functional Description

The IDT70V9189/79 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

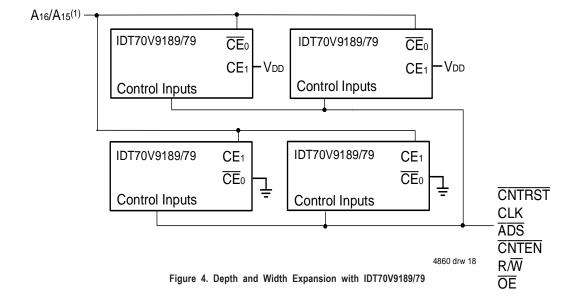
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to staff the operation of the address counters for fast interleaved memory applications.

 $\overline{\text{CE}}_0 = \text{VIH}$ or $\text{CE}_1 = \text{VIL}$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9189/79's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0 = \text{VIL}$ and $\text{CE}_1 = \text{VIH}$ to re-activate the outputs.

Depth and Width Expansion

The IDT70V9189/79 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

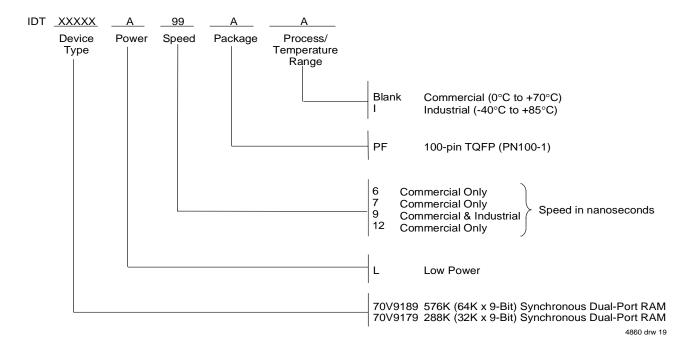
The IDT70V9189/79 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 18-bit or wider applications.



NOTE

1. A₁₆ is for IDT70V9189. A₁₅ is for IDT70V9179.

Ordering Information



IDT Clock Solution for IDT70V9189/79 Dual-Port

	Dual-Port I/O	Specitications		Clock Specif	IDT	IDT			
IDT Dual-Port Part Number	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement Maximum Frequency		Jitter Tolerance	PLL Clock Device	Non-PLL Clock Device	
70V9189/79	3.3	LVTTL	9pF	40%	100	150ps	2305 2308 2309	49FCT3805 49FCT3805D/E 74FCT3807 74FCT3807D/E	

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Datasheet Document History

9/30/99: Initial Public Release 11/12/99: Replaced IDT logo

1/10/01: Page 3 Changed information in Truth Table II

> Page 4 Increased storage temperature parameters

> > Clarified TA parameter

Page 5 DC Electrical parameters-changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes Removed Preliminary status

01/15/04: Consolidated multiple devices into one datasheet

Changed naming conventions from Vcc to Vdd and from GND to Vss

Removed I-temp footnote

Page 2 Added date revision to pin configuration

Added Junction Temperature to Absolute Maximum Ratings Table

Added Ambient Temperature footnote

Added I-temp numbers for 9ns speed to the DC Electrical Characteristics Table Page 5

Added 6ns speed DC power numbers to the DC Electrical Characteristics Table

Page 7 Added I-temp for 9ns speed to AC Electrical Characteristics Table

Added 6ns speed AC timing numbers to the AC Electrical Characteristics Table

Page 15 Added 6ns speed grade and 9ns I-temp to ordering information

Added IDT Clock Solution Table

